



175°C P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D T _C = +25°C
-40V	10mΩ @ V _{GS} = -10V	-50A
-40 v	14mΩ @ $V_{GS} = -4.5V$	-40A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Reverse Polarity Protection
- BLDC Motor Control
- Power Management Functions

Features and Benefits

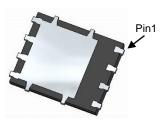
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production Low On-resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

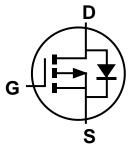
- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish 100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



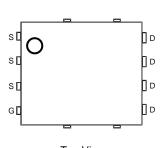




Bottom View



Internal Schematic



Top View Pin Configuration

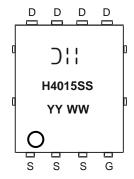
Ordering Information (Note 5)

Part Number	Case	Packaging	
DMPH4015SPSQ-13	PowerDI5060-8	2,500 / Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



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Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	-40	V		
Gate-Source Voltage	V_{GSS}	±25	V		
Continuous Drain Current V _{GS} = -10V (Note 7)	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	ΙD	-50 -35	А
Continuous Drain Current V _{GS} = -10V (Note 6)	Ι _D	-12.0 -9.0	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-100	Α		
Maximum Body Diode Continuous Current (Note 8)	Is	-50	Α		
Avalanche Current (Note 9) L = 1mH	I _{AS}	-22	A		
Avalanche Energy (Note 9) L = 1mH	E _{AS}	260	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	98	°C/W
Total Power Dissipation (Note 7)	T _A = +25°C	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	57.0	°C/W
Thermal Resistance, Junction to Case (Note 8)		ReJC	0.9	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage	BV_{DSS}	-40		_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	V _{GS(TH)}	-1.5	-2	-2.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	ם	_	8	10	mΩ	$V_{GS} = -10V, I_D = -9.8A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	11	14	1117.5	$V_{GS} = -4.5V, I_D = -9.8A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	Ciss	_	4234	_			
Output Capacitance	Coss	_	1036	_	pF	$V_{DS} = -20V, V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	C_{rss}	_	526	_		I = IIVIDZ	
Gate Resistance	R_g	_	7.8	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_g	_	42.7	_			
Total Gate Charge (V _{GS} = -10V)	Q_g	_	91	_	nC	$V_{DS} = -20V,$ $I_{D} = -9.8A$	
Gate-Source Charge	Q _{gs}	_	14.2	_	nc		
Gate-Drain Charge	Q _{gd}	_	13.5	_			
Turn-On Delay Time	t _{D(ON)}	_	13.2	_		$V_{GS} = -10V, V_{DD} = -20V,$ $R_{G} = 6\Omega, I_{D} = -1A$	
Turn-On Rise Time	t _R	_	10	_			
Turn-Off Delay Time	t _{D(OFF)}	_	303	_	ns		
Turn-Off Fall Time	t _F	_	138	_			
Reverse Recovery Time	t _{RR}	_	26	_	ns	I _F = -9.8A, di/dt = -100A/μs	
Reverse Recovery Charge	Q _{RR}	_	20	_	nC	I _F = -9.8A, di/dt = -100A/μs	

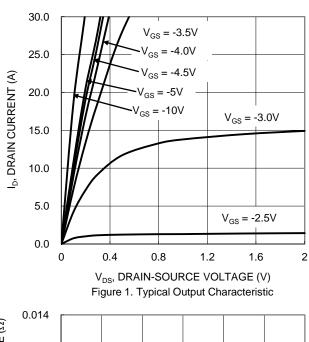
6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

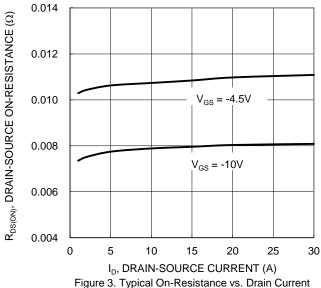
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 8. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 9. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25$ °C.
- 10. Short duration pulse test used to minimize self-heating effect.

 11. Guaranteed by design. Not subject to product testing.









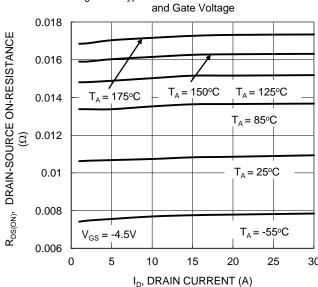


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

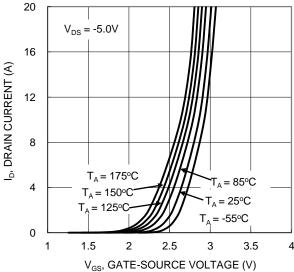


Figure 2. Typical Transfer Characteristic

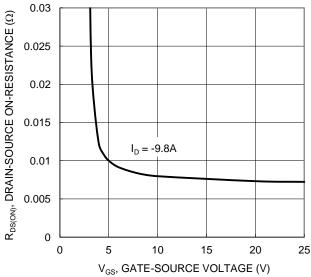


Figure 4. Typical Transfer Characteristic

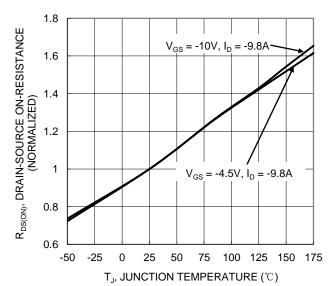
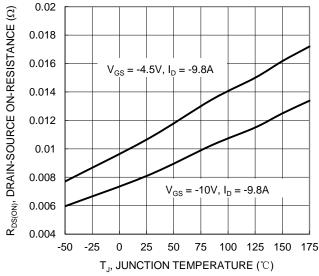


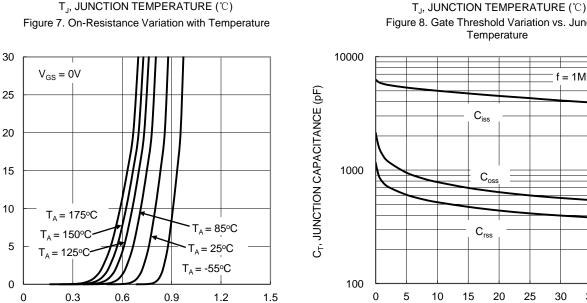
Figure 6. On-Resistance Variation with Temperature



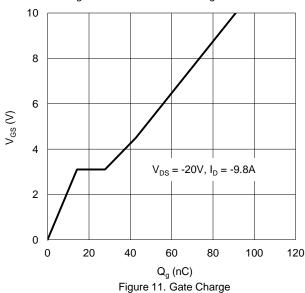


Is, SOURCE CURRENT (A)



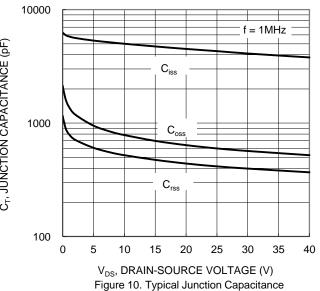


 V_{SD} , SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



2.2 $V_{GS(TH)}$, GATE THRESHOLD VOLTAGE (V) 2 $I_D = -1mA$ 1.8 1.6 $I_{D} = -250 \mu A$ 1.4 1.2 1 -25 50 75 100 125 150 -50

Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R_{DS(ON)} 100 ID, DRAIN CURRENT (A) 10 T_{J(Max)} = 175°C T_A = 25 °C 0.1 Single Pulse = 100ms DUT on 1*MRP Board $V_{GS} = -10V$ $P_W = 10ms$ 0.01 0.01 1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



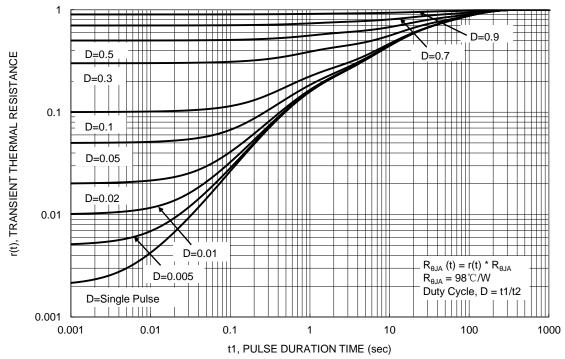


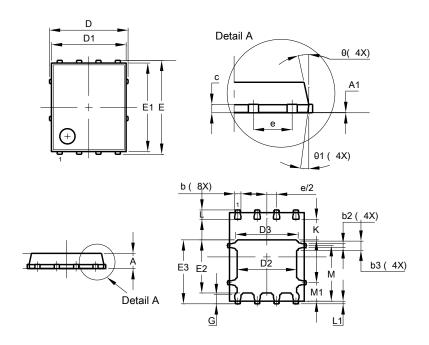
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

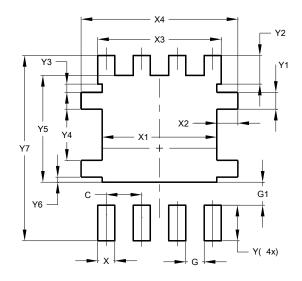


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
C	0.230	0.330	0.277		
D	į,	5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(6.15 BSC			
E1	5.60	6.00	5.80		
E2	3.28 3.68		3.48		
E3	3.99 4.39 4.19				
е		1.27 BSC	;		
G	0.51	0.71	0.61		
K	0.51	-	-		
٦	0.51 0.71 0.				
L1	0.100 0.200 0.1		0.175		
M	3.235 4.035 3.		3.635		
M1			1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)				
С	1.270				
G	0.660				
G1	0.820				
X	0.610				
X1	4.100				
X2	0.755				
Х3	4.420				
X4	5.610				
Y	1.270				
Y1	0.600				
Y2	1.020				
Y3	0.295				
Y4	1.825				
Y5	3.810				
Y6	0.180				
Y7	6.610				



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